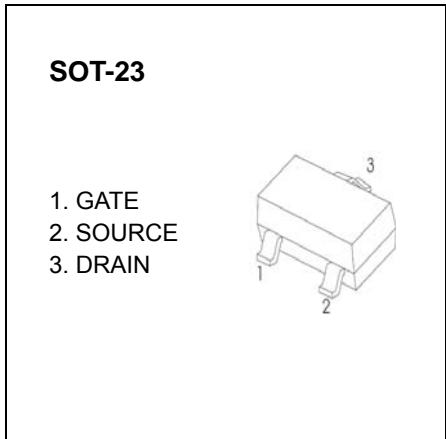
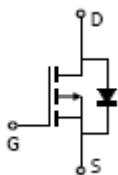


SOT-23 Plastic-Encapsulate MOSFETS

CJ2321 P-Channel 20-V(D-S) MOSFET

APPLICATIONS

- PA Switch
- Load Switch



MARKING: S21

Maximum ratings (T_a=25°C unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	-20	V
Gate-Source Voltage	V _{GS}	±12	
Continuous Drain Current	I _D	-2.9	A
Pulsed Drain Current	I _{DM}	-12	
Continuous Source-Drain Diode Current	I _S	-0.59	
Maximum Power Dissipation	P _D	0.35	W
Thermal Resistance from Junction to Ambient	R _{θJA}	357	°C/W
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-50 ~+150	

Electrical characteristics (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -10μA	-20			V
Gate-source leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V			±100	nA
Zero Gate voltage drain current	I _{DSS}	V _{DS} = -16V, V _{GS} = 0V			-1.0	μA
Gate-source threshold voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.4		-0.9	V
Drain-source on-state resistance	R _{DS(on)}	V _{GS} = -4.5V, I _D = -3.3A			0.057	Ω
		V _{GS} = -2.5V, I _D = -2.8A			0.076	
		V _{GS} = -1.8V, I _D = -2.3A			0.110	
Forward transconductance	g _{fS}	V _{DS} = -5V, I _D = -3.3A	3			S
Forward diode voltage	V _{SD}	V _{GS} = 0V, I _S = -1.6A			-1.2	V
Dynamic						
Input capacitance ^{a,b}	C _{iss}	V _{DS} = -6V, V _{GS} = 0V, f = 1MHz		715		pF
Output capacitance ^{a,b}	C _{oss}			170		
Reverse transfer capacitance ^{a,b}	C _{rss}			120		
Total Gate charge ^a	Q _g	V _{DS} = -6V, V _{GS} = -4.5V, I _D = -3.3A			13	nc
Gate-Source charge ^a	Q _{gs}			1.2		nc
Gate-Drain charge ^a	Q _{gd}			2.2		nc
Switching^{a,b}						
Turn-on delay Time	t _{d(on)}	V _{GEN} = -4.5V, V _{DD} = -6V, I _D = -1.0A, R _G = 6Ω, R _L = 6Ω			25	ns
Rise time	t _r				55	
Turn-off delay time	t _{d(off)}				90	
Fall time	t _f				60	

Notes :

a. Pulse Test : pulse width ≤300μs, duty cycle ≤2%.

